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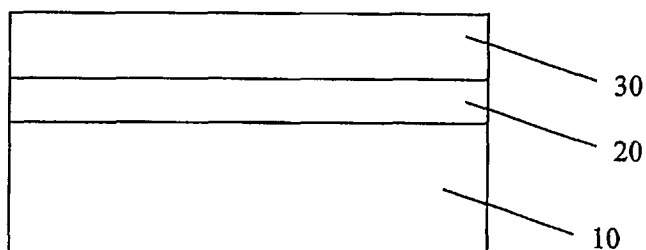
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(54) Title: SILICIDE FORMED FROM TERNARY METAL ALLOY FILMS



(57) Abstract: A NiSi layer over silicon that is thermally stable and can form even in the presence of oxides (20). The method of fabricating the nickel silicide layer includes providing a substrate comprising silicon (10), depositing a layer of at least a 3-component metal alloy (30) comprising nickel on a surface of the substrate, and annealing the alloy and the substrate. The annealing temperature is less than 1000°C. The 3-component metal alloy can include Ni, Ti and Pt.



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